L Number	Hits	Search Text	DB	Time stamp
1	2886573	memory or storage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 15:24
2	395	(memory or storage) and flash and sonos	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 15:25
3	1316	(memory or storage) and silicon adj oxide adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 15:27
4	1563	((memory or storage) and flash and sonos) ((memory or storage) and silicon adj oxide adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 15:27
5	27	(((memory or storage) and flash and sonos) ((memory or storage) and silicon adj oxide adj nitride)) and program$7 with hot adj electron with nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 16:21
6	15	((((memory or storage) and flash and sonos) ((memory or storage) and silicon adj oxide adj nitride)) and program$7 with hot adj electron with nitride) and (voltage or potential or level) with substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 15:29
7	15	(((((memory or storage) and flash and sonos) ((memory or storage) and silicon adj oxide adj nitride)) and program$7 with hot adj electron with nitride) and (voltage or potential or level) with substrate) and (voltage or potential or level) with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 15:30
8	10	((((((memory or storage) and flash and sonos) ((memory or storage) and silicon adj oxide adj nitride)) and program$7 with hot adj electron with nitride) and (voltage or potential or level) with substrate) and (voltage or potential or level) with gate) and (fowler or hot adj hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 16:06
9	10	(((((((memory or storage) and flash and sonos) ((memory or storage) and silicon adj oxide adj nitride)) and program$7 with hot adj electron with nitride) and (voltage or potential or level) with substrate) and (voltage or potential or level) with gate) and (fowler or hot adj hole)) and eras$5	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 16:07
10	11	(((memory or storage) and flash and sonos) ((memory or storage) and silicon adj oxide adj nitride)) and eras$5 with (fowler or hot adj hole) with (voltage or potential or level) with substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 16:23
11	87	(((memory or storage) and flash and sonos) ((memory or storage) and silicon adj oxide adj nitride)) and eras$5 with float$5 with (drain or source)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 16:23
12	5	((((memory or storage) and flash and sonos) ((memory or storage) and silicon adj oxide adj nitride)) and eras$5 with (fowler or hot adj hole) with (voltage or potential or level) with substrate) and ((((memory or storage) and flash and sonos) ((memory or storage) and silicon adj oxide adj nitride)) and eras$5 with float$5 with (drain or source))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 16:23